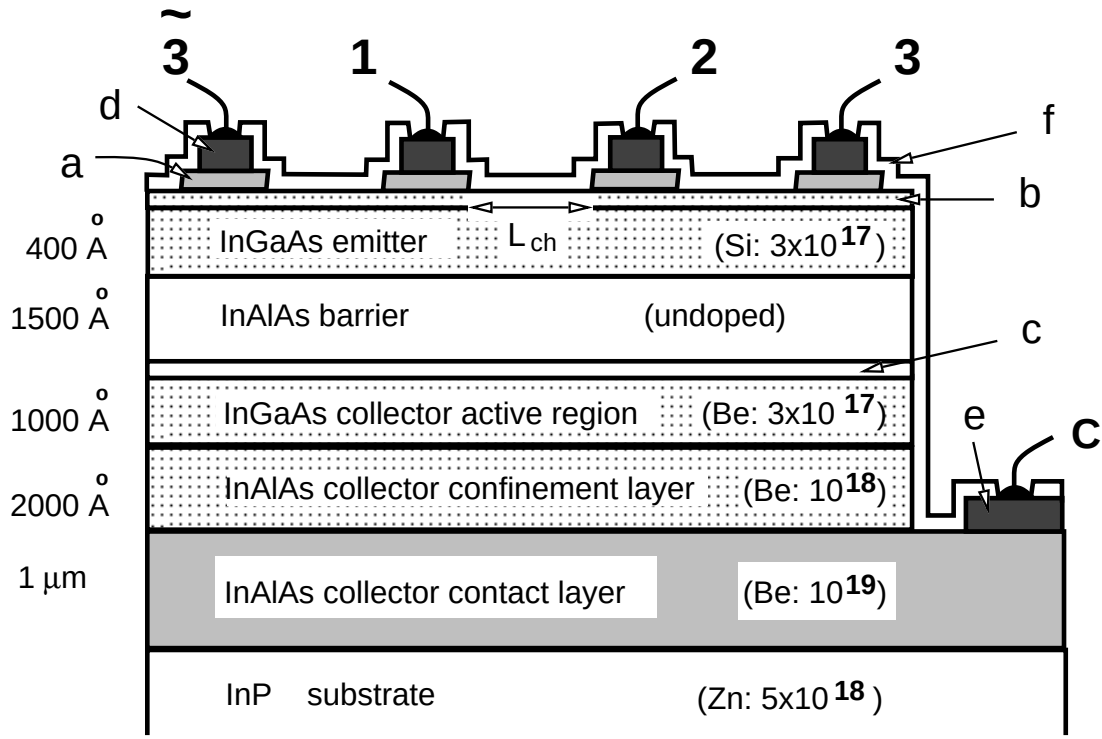

a: 200 Å InGaAs, n (Sn: 10^{20})

b: 25 Å InAlAs, n (Sn: 10^{19})

c: 15 Å InGaAs (undoped)

d: 300 Å Ti / 1800 Å Au

e: 800 Å AuBe / 2000 Å Au

f: 1500 Å Si_3N_4